



501.42841X00

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): KUMAGAI, et al.  
Serial No.: 10/625,616  
Filed: July 24, 2003  
For: SEMICONDUCTOR DEVICE INCLUDING N-CHANNELED  
FETs AND P-CHANNELED FETs WITH IMPROVED DRAIN  
CURRENT CHARACTERISTICS (*As Amended*)  
Group: 2811 Exr. H. Vu

**AMENDMENT**

Commissioner of Patents  
POB 1450  
Alexandria, VA 22313-1450

August 3, 2005

Sir:

In response to the Office Action dated May 3, 2005, please amend the above-identified application as listed below and as set forth on the following pages:

**Amendments to the Title;**

**Amendments to the Claims; and**

**Remarks are included following the amendments.**